

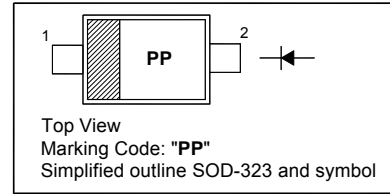
# 1N728WS

## Silicon Epitaxial Planar Schottky Barrier Diode

For super-high speed switching and wave detection circuit applications

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

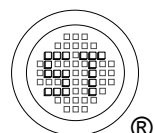


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

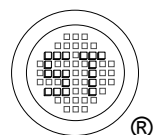
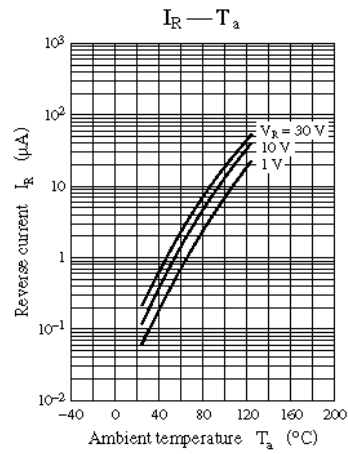
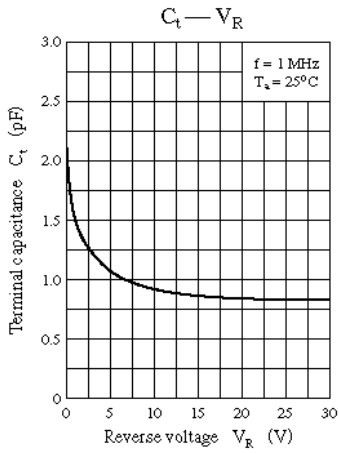
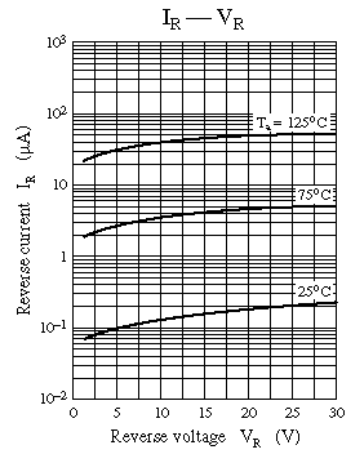
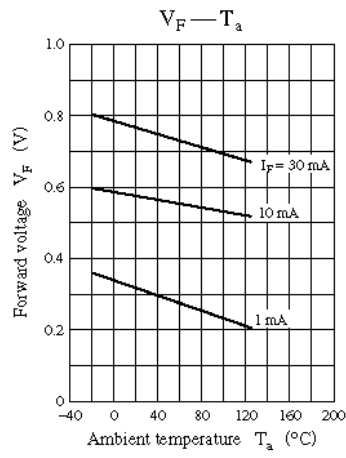
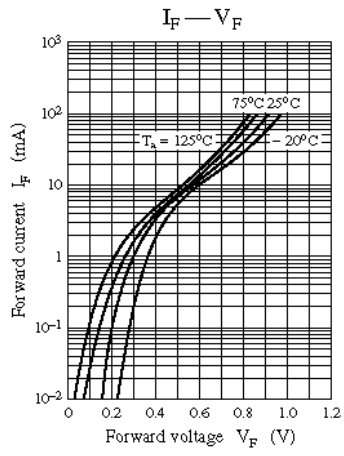
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	30	V
Reverse Voltage	$V_R$	30	V
Forward Current	$I_F$	30	mA
Peak Forward Current	$I_{FM}$	150	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 30\text{ mA}$	$V_F$	- -	0.4 1	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	0.3	$\mu\text{A}$
Terminal Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	1.5	-	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$ , $I_{rr} = 1\text{ mA}$ , $R_L = 100\ \Omega$	$t_{rr}$	1	-	ns
Detection Efficiency at $V_{in} = 3\text{ V}_{(peak)}$ , $f = 30\text{ MHz}$ , $R_L = 3.9\text{ K}\Omega$ , $C_L = 10\text{ pF}$	$\eta$	65	-	%



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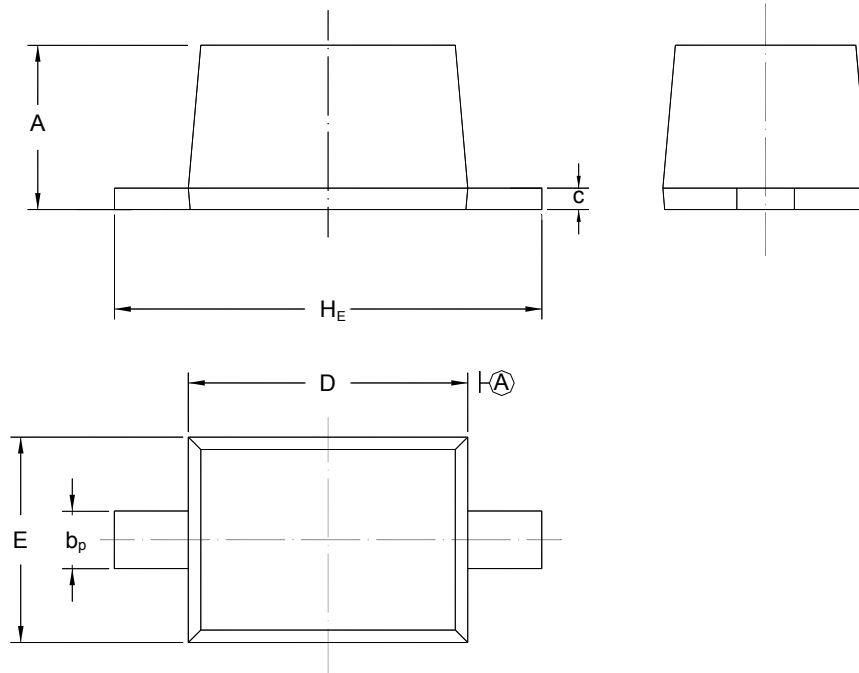


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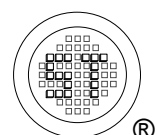
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>
mm	1.10 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30



Dated : 01/09/2006